

Large Time Behavior of Multi-dimensional Unipolar Hydrodynamic Model of Semiconductor

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ABSTRACT

In this paper, we are concerned with the large time behavior of weak entropy solutions to the multi-dimensional unipolar hydrodynamic model of semiconductor with insulating boundary conditions and non-zero doping profile. For any space dimension, we prove the solutions converge to the stationary solutions exponentially in time. No smallness conditions are assumed.

Keywords: Large time behavior; Unipolar hydrodynamic model; Insulating boundary conditions; Non-zero doping profile

INTRODUCTION

In this paper, we consider the following unipolar hydrodynamic model of semiconductor:

$$\begin{cases} \partial_t n + \nabla \cdot \mathbf{J} = 0, \\ \partial_t \mathbf{J} + \nabla \cdot \left(\frac{\mathbf{J} \otimes \mathbf{J}}{n} \right) + \nabla p(n) = n\mathbf{E} - \mathbf{J}, \\ \nabla \cdot \mathbf{E} = n - D(x) \end{cases} \quad (1.1)$$

Where $(x, t) \in \Omega \times (0, \infty)$ with Ω being a bounded open set in \mathbb{R}^d , $d \geq 1$. The unknowns $n(x, t) > 0$, $\mathbf{J}(x, t)$ represent the scaled partial density and current density of the electrons. The unknown function \mathbf{E} denotes the electric field, which is generated by the Coulomb force of particles. If we introduce the electrostatic potential ϕ then $\mathbf{E} = \nabla \phi$. In this paper, we consider the isothermal case $p(n) = n$, which is of importance in industry. The symbols \otimes and $(\nabla \cdot)$ denote the Kronecker tensor product and the divergence in \mathbb{R}^d . $D(x) > 0$ is the doping profile, which means the density of impurities in semiconductor materials. We suppose.

$$D(x) \in C^2(\mathbb{R}), \quad D^* = \sup_x D(x) \geq \inf_x D(x) = D_* > 0 \quad (1.2)$$

In this paper, we consider problem (1.1) with the initial conditions

$$n(x, 0) = n_0(x) > 0, \quad \mathbf{J}(x, 0) = \mathbf{J}_0(x), \quad (1.3)$$

And the following insulating boundary conditions

$$\mathbf{J}(x, t) \cdot \mathbf{n}|_{\partial\Omega} = 0, \quad \mathbf{E}(x, t) \cdot \mathbf{n}|_{\partial\Omega} = 0 \quad (1.4)$$

Where \mathbf{n} is the outer unit normal vector on $\partial\Omega$.

Now let's recall some known results for the model (1.1). The existence and uniqueness of the subsonic steady solutions was

first established by Degond- Markowich, Gamba investigated the stationary transonic solutions [1-5]. For the time dependent model, Hsiao-Yang, Luo-Natalini-Xin and Guo-Strauss proved the existence of global smooth solutions near a given steady state for different kinds of initial or initial-boundary conditions [6-14]. However, Chen proved the existence of the local generalized solutions and gave the blow up phenomenon of this equation [3]. Therefore, it is necessary to study weak solutions. The existence result of weak solutions was given in [7,15-26]. Huang and Yu proved the weak solutions converge to the stationary solutions exponentially in time when space dimension [9,25]. For more results about the unipolar model of semiconductor, we can refer to [1,8,10-12,14,16-20].

In this paper, our main goal is to prove the exponential convergence of multi-dimensional unipolar hydrodynamic model of semiconductor with insulating boundary conditions and non-zero doping profile. That is, all weak entropy solutions of problem (1.1) (1.3) (1.4) converge to the corresponding stationary system.

$$\begin{cases} \nabla \tilde{n} = \tilde{n} \tilde{\mathbf{E}}, \\ \nabla \cdot \tilde{\mathbf{E}} = \tilde{n} - D(x) \\ \tilde{\mathbf{E}} \cdot \mathbf{n}|_{\partial\Omega} = 0, \end{cases} \quad (1.5)$$

With an exponential decay rate, when $d=1,2$, the existence to smooth solution of problem (1.5) can be proved by variation method [6].

Before stating the main result, we first give the definition of weak entropy solution and some common notations.

Definition 1.1. A For every $T > 0$, the function $(n, \mathbf{J}, \mathbf{E})(x, t) \in (L^2(\Omega \times [0, T]))^{2d+1}$ is said to be a L^2

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weak solution of problem (1.1)(1.3)(1.4) if,

$$\begin{cases} \int_0^T \int_{\Omega} (n\varphi_t + \mathbf{J} \cdot \nabla_x \varphi) dx dt + \int_{\Omega} n_0 \varphi(x,0) dx = 0, \\ \int_0^T \int_{\Omega} (\mathbf{J} \varphi_t + (\frac{\mathbf{J} \otimes \mathbf{J}}{n} + p(n) \nabla_x \varphi) dx dt + \int_0^T \int_{\Omega} (n\mathbf{E} - \mathbf{J}) \varphi dx dt \\ + \int_{\Omega} \mathbf{J}_0 \varphi(x,0) dx = 0, \\ \int_0^T \int_{\Omega} \mathbf{E} \cdot \nabla_x \varphi dx dt + \int_0^T \int_{\Omega} (n - D(x) \varphi) dx dt = 0, \end{cases} \quad (1.6)$$

For all $\varphi \in H_0^1(\Omega \times [0, T])$, with $\varphi(\cdot, t)|_{\partial\Omega} = 0$ and $\varphi(\cdot, t)|_{\partial\Omega} = 0$, and \mathbf{J}, \mathbf{E} satisfies

In the sense of trace. Furthermore, a weak solution of system (1.1) (1.3) (1.4) is called an entropy solution if the following entropy solution if the following entropy inequality.

$$\frac{\partial \eta}{\partial t}(n, \mathbf{J}) + \partial_r q^r(n, \mathbf{J}) + \frac{\mathbf{J}}{n} \cdot (\mathbf{J} - n\mathbf{E}) \leq 0, \quad (1.7)$$

Hold in the distributional sense, where (1.7) use the Einstein's summation symbols (η, q) , is entropy flux pair satisfying.

$$\begin{cases} \eta(n, \mathbf{J}) = \frac{|\mathbf{J}|^2}{2n} + n \mathbf{h} \cdot n, \\ q^r(n, \mathbf{J}) = (\frac{|\mathbf{J}|^2}{2n} + n(1 + \mathbf{h} \cdot n)) \frac{J^r}{n}. \end{cases} \quad (1.8)$$

Let $\mathbf{U} = (n, \mathbf{J})^T, \tilde{U} = (\tilde{n}, \mathbf{0})^T, \|f\| = \|f\|_2 = (\int |f(x)|^2 dx)^{1/2}$

$\mathbf{J} = (J^1, J^2, \dots, J^d)$ and we choose $C_i (i = 0, 1, 2, \dots)$ to represent different positive constants in different places.

The main result of this paper is given below.

Theorem 1.1. Suppose $(\tilde{u}, \tilde{\mathbf{E}})(x) = (\tilde{n}, \mathbf{0}, \tilde{\mathbf{E}})(x)$ is a smooth solution of problem (1.5), $(\mathbf{U}, \mathbf{E})(x, t) = (n, \mathbf{J}, \mathbf{E})(x, t)$ is any L^2 weak entropy solution of problem (1.1)(1.3)(1.4). If there exist positive constants N^*, N_* and C_0 such that,

$$N_* \leq \tilde{n}(x) \leq N^*, \quad (1.9)$$

$$0 \leq n(x, t) \leq C_0, \quad (1.10)$$

For any $x \in \Omega, t > 0$, then

$$\int_{\Omega} (n - \tilde{n})^2 + \frac{|\mathbf{J}|^2}{n} + |\mathbf{E} - \tilde{\mathbf{E}}|^2 dx \leq \alpha e^{-\beta t} \int_{\Omega} (n - \tilde{n})^2 + \frac{|\mathbf{J}|^2}{n} + |\mathbf{E} - \tilde{\mathbf{E}}|^2 dx + \int_{\Omega} (\tilde{u} - \tilde{\mathbf{E}})^2 dx + \int_{\Omega} \tilde{u} \tilde{\mathbf{E}} dx + \int_{\Omega} \tilde{u} \tilde{\mathbf{E}} dx + \int_{\Omega} \tilde{u} \tilde{\mathbf{E}} dx + \int_{\Omega} \tilde{u} \tilde{\mathbf{E}} dx \quad (2.9)$$

Holds for some positive constants α and β .

THE PROOF OF THEOREM 1.1

From equations (1.1) and (1.5), we obtain the following system.

$$\begin{cases} \partial_t (n - \tilde{n}) + \nabla \cdot \mathbf{J} = 0, \\ \partial_t \mathbf{J} + \nabla \cdot (\frac{\mathbf{J} \otimes \mathbf{J}}{n}) + \nabla (n - \tilde{n}) = (n\mathbf{E} - \tilde{n}\tilde{\mathbf{E}}) - \mathbf{J}, \\ \nabla \cdot (\mathbf{E} - \tilde{\mathbf{E}}) = (n - \tilde{n}) = \Delta(\phi - \tilde{\phi}), \end{cases} \quad (2.1)$$

Satisfies in the sense of Definition 1.1.

The proof of Theorem 1.1 is completed in the following two theorem.

Theorem 2.1. Suppose $(\mathbf{U}, \mathbf{E})(x, t)$ be a weak entropy solution of (1.1)(1.3)(1.4) in the time interval $[0, T]$, $[\tilde{U}, \tilde{\mathbf{E}}]$ is a smooth solution of problem (1.5), If (1.9) and (1.10) satisfy for any $x \in \Omega$ and $t > 0$, then,

$$\int ((n - \tilde{n}) + \frac{|\mathbf{J}|}{n}) + |\mathbf{E} - \tilde{\mathbf{E}}| dx \leq C \int ((n - \tilde{n}) + \frac{|\mathbf{J}|}{n}) + |\mathbf{E} - \tilde{\mathbf{E}}| dx, \quad (2.2)$$

Holds for some positive constants C_1

Proof: Using Einstein's summation convention, we can rewrite the first $d + 1$

equations of (1.1) as a hyperbolic system of conservation laws.

$$\partial_t \mathbf{U} + \partial_r \mathbf{w}^r = \mathbf{F}(\mathbf{U}, \mathbf{E}) \quad (2.3)$$

Where,

$$\mathbf{w}^1 = \begin{pmatrix} J^1 \\ n + (J^1)^2/n \\ J^1 J^2/n \\ \dots \\ J^1 J^d/n \end{pmatrix}, \quad \mathbf{w}^2 = \begin{pmatrix} J^2 \\ n + (J^2)^2/n \\ \dots \\ J^2 J^d/n \end{pmatrix}, \dots, \quad \mathbf{w}^d = \begin{pmatrix} J^d \\ J^1 J^d/n \\ J^2 J^d/n \\ \dots \\ n + (J^d)^2/n \end{pmatrix} \quad (2.5)$$

$$\mathbf{F}(\mathbf{U}, \mathbf{E}) = (0, n\mathbf{E} - \mathbf{J})^T$$

From (1,7), we obtain

$$\frac{\partial \eta}{\partial t}(\mathbf{U}) + \partial_r q^r(\mathbf{U}) \leq g(\mathbf{U}, \mathbf{E}) \quad (2.6)$$

With the energy production

$$g(\mathbf{U}, \mathbf{E}) = -\frac{|\mathbf{J}|^2}{n} + \mathbf{J} \cdot \mathbf{E}$$

Let,

$$\tilde{\eta} = \eta - Q, \quad \tilde{q}^r = q^r - P^r \quad (2.7)$$

Where,

$$Q = \tilde{n} \ln \tilde{n} + (\ln \tilde{n} + 1)(n - \tilde{n}), \quad P^r = (\ln \tilde{n} + 1)J^r \quad (2.8)$$

From(1.5) and (2.6) - (2.8), we obtain

$$0 \geq \partial_t \tilde{\eta} + \partial_r \tilde{q}^r + \frac{|\mathbf{J}|^2}{n} - \mathbf{J} \cdot \mathbf{E}$$

$$= \partial_t \tilde{\eta} + \partial_r \tilde{q}^r + \frac{|\mathbf{J}|^2}{n} - \mathbf{J} \cdot \mathbf{E} + \mathbf{J} \cdot \tilde{\mathbf{E}} \quad (2.9)$$

Integrating the last equation in (2.9) over Ω and using the boundary condition (1.4), we get

$$\frac{d}{dt} \int \tilde{\eta} dx \leq - \int \frac{|\mathbf{J}|^2}{n} dx + \int (\mathbf{E} - \tilde{\mathbf{E}}) \cdot \mathbf{J} dx \quad (2.10)$$

On the other hand, after integrating by parts and using the boundary condition (1.4) for several times, we obtain

$$\frac{d}{dt} \int \frac{1}{2} |\mathbf{E} - \tilde{\mathbf{E}}|^2 dx = \int (\mathbf{E} - \tilde{\mathbf{E}}) \cdot \partial_r (\mathbf{E} - \tilde{\mathbf{E}}) dx = - \int (\mathbf{E} - \tilde{\mathbf{E}}) \cdot \mathbf{J} dx. \quad (2.11)$$

Combining (2.10) with (2.11), we obtain

$$\frac{d}{dt} \int (\eta + |\mathbf{E} - \tilde{\mathbf{E}}|^2) dx \leq - \int \frac{|\mathbf{J}|^2}{n} dx \leq \quad (2.12)$$

Moreover, we notice that $\tilde{\eta}$

is the quadratic remainder of the Taylor expansion of the convex function $n \ln n$ around $\tilde{n} > N_* > 0$. Therefore, using (1.9) and (1.10), we obtain there exist positive constants C_2 and C_3 such that,

$$C_2(n - \tilde{n})^2 + \frac{|J|^2}{n} \leq \tilde{\eta} \leq C_3(n - \tilde{n})^2 + \frac{|J|^2}{n}.$$

We finish the proof of Theorem 2.1.

Theorem 2.2. Under the same assumptions as in Theorem 2.1, we further have the exponential decay rate, that is,

$$\int ((n - \tilde{n}) + \frac{|J|}{n} + |E - \tilde{E}|) dx \leq \alpha e^{-\beta \int ((n - \tilde{n}) + \frac{|J|}{n} + |E - \tilde{E}|) dx},$$

For some positive constants α and β .

Proof: To get the exponential decay rate, we would like to use the Gronwall inequality. To do this we define,

$$W = \tilde{\eta} + \frac{1}{2}|E - \tilde{E}| + \mu \left\{ -(E - \tilde{E}) \cdot J + \frac{1}{2}|E - \tilde{E}| \right\} \quad (2.13)$$

Where μ

is a real number which will be determined later? In terms of (2.1)₂ and the boundary condition (1.4), we get,

$$\begin{aligned} & -\frac{d}{dt} \int (E - \tilde{E}) \cdot J dx \\ &= -\int (E - \tilde{E}) \cdot J dx - \int (E - \tilde{E}) \cdot J dx \\ &= \int |E - \tilde{E}| dx + \int (E - \tilde{E}) \cdot \left\{ \nabla \cdot \left(\frac{J \otimes J}{n} \right) + \nabla(n - \tilde{n}) - (nE - \tilde{n}\tilde{E}) + J \right\} dx. \end{aligned}$$

We calculate the right side of (2.14) item by item. Firstly, using Young's inequality, we have,

$$\begin{aligned} \int |E - \tilde{E}| dx &= -\int (E - \tilde{E}) \cdot J dx \\ &\leq \frac{1}{2} \int |E - \tilde{E}| dx + \frac{1}{2} \int |J|^2 dx, \end{aligned} \quad (2.15)$$

Which gives,

$$\int |E - \tilde{E}| dx \leq \int |J|^2 dx \quad (2.16)$$

We also have,

$$\begin{aligned} \int (E - \tilde{E}) \cdot \left\{ \nabla \cdot \left(\frac{J \otimes J}{n} \right) \right\} dx &= C \int \frac{1}{n} (\nabla \cdot (E - \tilde{E})) \cdot |J| dx \\ &\leq C \int \left| \frac{n - \tilde{n}}{n} \right| |J| dx, \end{aligned} \quad (2.17)$$

$$\begin{aligned} \int (E - \tilde{E}) \cdot (\nabla(n - \tilde{n})) dx &= -\int \nabla \cdot (E - \tilde{E}) \cdot (n - \tilde{n}) dx \\ &= -\int (n - \tilde{n}) dx. \end{aligned} \quad (2.18)$$

Notice

$$-\int (n - \tilde{n}) \tilde{E} \cdot (E - \tilde{E}) dx = -\int (\nabla \cdot (E - \tilde{E})) \tilde{E} \cdot (E - \tilde{E}) dx \quad (2.19)$$

We obtain

$$\begin{aligned} &= \int \frac{\nabla \cdot \tilde{E}}{2} |E - \tilde{E}| dx, \\ & -\int (E - \tilde{E}) \cdot (nE - \tilde{n}\tilde{E}) dx \\ &= -\int \tilde{n} |E - \tilde{E}| dx - \int (n - \tilde{n}) \tilde{E} \cdot (E - \tilde{E}) dx - \int (n - \tilde{n}) |E - \tilde{E}| dx \\ &= \int \left(\frac{\nabla \cdot \tilde{E}}{2} - \tilde{n} \right) |E - \tilde{E}| dx \leq -\left(\frac{N}{2} + \frac{D}{2} \right) \int |E - \tilde{E}| dx, \end{aligned} \quad (2.20)$$

Where we have used (1.5)₂ and the fact that

$$\frac{\tilde{n}}{2} + \frac{D(x)}{2} \geq \frac{N_*}{2} + \frac{D_*}{2}.$$

From the above analysis (2.14)-(2.20) and (2.11) (2.12), we deduce

$$\frac{d}{dt} \int W dx \leq -\int Y dx, \quad (2.21)$$

Which

$$Y = (1 - \mu m - \mu C_4 |n - \tilde{n}|) \frac{|J|^2}{n} + \mu(n - \tilde{n})^2 + \mu \left(\frac{N_*}{2} + \frac{D_*}{2} \right) |E - \tilde{E}|^2. \quad (2.22)$$

As the proof in [2], we can choose μ

small enough such that W and Y are positive definite quadratic forms. So there exist positive constants K_w and K_y such that,

$$K \int \left((n - \tilde{n}) + \frac{|J|}{n} + |E - \tilde{E}| \right) dx \leq \int W dx, \quad (2.23)$$

$$K \int \left((n - \tilde{n}) + \frac{|J|}{n} + |E - \tilde{E}| \right) dx \leq \int Y dx, \quad (2.24)$$

The estimate (2.21) turns into

$$\frac{d}{dt} \int W dx \leq -K \int \left((n - \tilde{n}) + \frac{|J|}{n} + |E - \tilde{E}| \right) dx, \quad (2.25)$$

From Gronwall inequality we get Theorem 2.2, with $\beta = K_y / K_w$

By Theorem 2.2 we can easily deduce Theorem 1.1.

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